

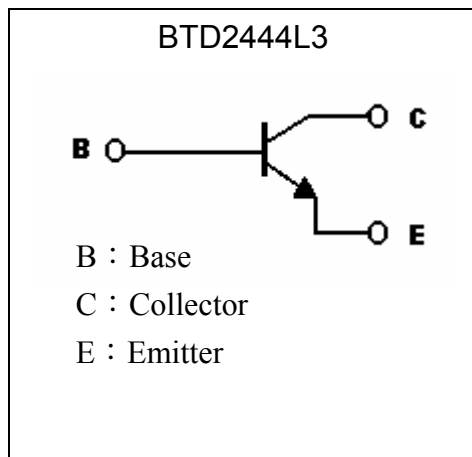
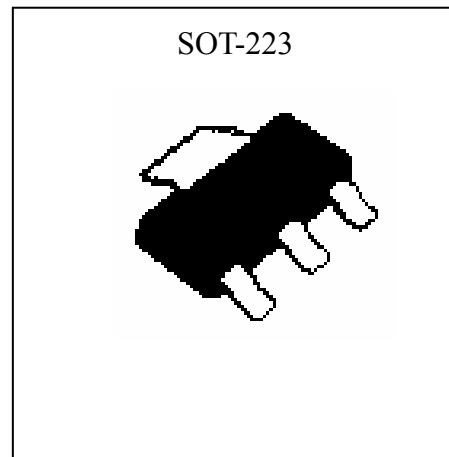
**Low Vcesat NPN Epitaxial Planar Transistor**

# BTD2444L3

$BV_{CEO}$	20V
$I_C$	1A
$R_{CESAT}$	0.35 $\Omega$ (typ.)

**Features**

- The BTD2444L3 is designed for general purpose low frequency power amplifier applications.
- Low  $V_{CE(sat)}$ ,  $V_{CE(sat)}=0.35V$  (typ), at  $I_C / I_B = 1A / 50mA$
- Complementary to BTB1590L3
- Pb-free lead plating and halogen-free package

**Symbol**

**Outline**

**Absolute Maximum Ratings** ( $T_a=25^\circ C$ )

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	$V_{CBO}$	40	V
Collector-Emitter Voltage	$V_{CEO}$	25	V
Emitter-Base Voltage	$V_{EBO}$	6	V
Collector Current (DC)	$I_C$	1	A
Collector Current (Pulse)	$I_{CP}$	3 (Note)	A
Base Current	$I_B$	0.2	A
Power Dissipation @ $T_A=25^\circ C$	$P_D$	1	W
Power Dissipation @ $T_C=25^\circ C$		3	
Operating Junction Temperature Range	$T_j$	-55~+150	$^\circ C$
Storage Temperature Range	$T_{stg}$	-55~+150	$^\circ C$

 Note : Single pulse,  $P_w=10ms$

**Thermal Data**

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to- ambient, max	$R_{th,j-a}$	125	°C/W
Thermal Resistance, Junction-to- case, max	$R_{th,j-c}$	41.7	°C/W

**Characteristics (Ta=25°C)**

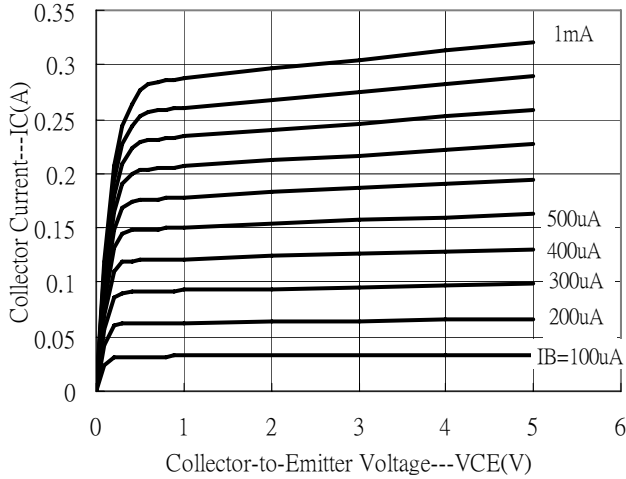
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
$BV_{CBO}$	40	-	-	V	$I_C=100\mu A, I_E=0$
$BV_{CEO}$	25	-	-	V	$I_C=2mA, I_B=0$
$BV_{EBO}$	6	-	-	V	$I_E=100\mu A, I_C=0$
$I_{CBO}$	-	-	0.5	$\mu A$	$V_{CB}=30V, I_E=0$
$I_{EBO}$	-	-	0.5	$\mu A$	$V_{EB}=6V, I_C=0$
* $V_{CE(sat)1}$	-	0.15	0.3	V	$I_C=400mA, I_B=20mA$
* $V_{CE(sat)2}$	-	0.35	0.5	V	$I_C=1A, I_B=50mA$
* $R_{CE(sat)}$	-	0.35	0.5	$\Omega$	$I_C=1A, I_B=50mA$
* $V_{BE(on)}$	-	-	1	V	$V_{CE}=1V, I_C=1A$
* $h_{FE1}$	180	-	390	-	$V_{CE}=1V, I_C=100mA$
* $h_{FE2}$	60	-	-	-	$V_{CE}=1V, I_C=1A$
$f_T$	100	-	-	MHz	$V_{CE}=5V, I_C=50mA, f=100MHz$
Cob	-	6	-	pF	$V_{CB}=10V, f=1MHz$

\*Pulse Test : Pulse Width  $\leq 380\mu s$ , Duty Cycle  $\leq 2\%$ **Ordering Information**

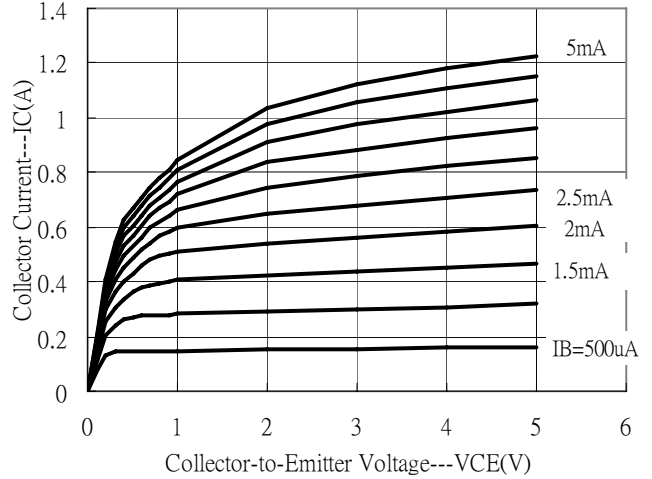
Device	Package	Shipping
BTD2444L3-0-T3-G	SOT-223 (Pb-free lead plating and halogen-free package)	2500 pcs / Tape & Reel

**Typical Characteristics**

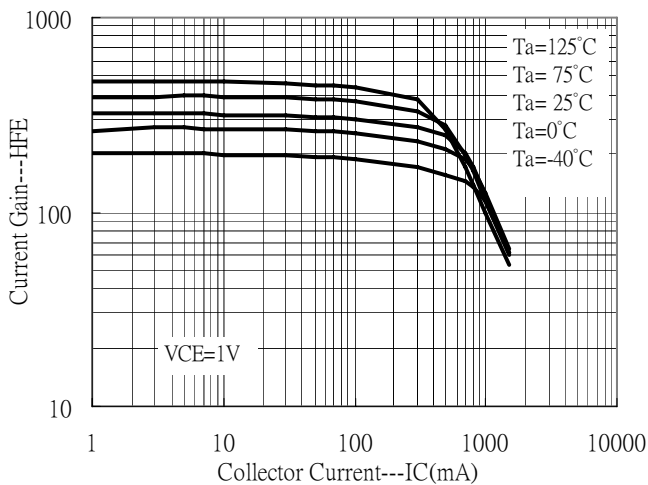
Emitter Grounded Output Characteristics



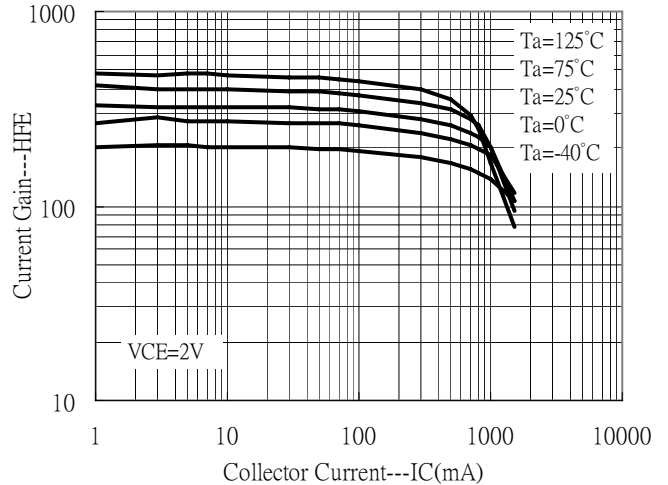
Emitter Grounded Output Characteristics



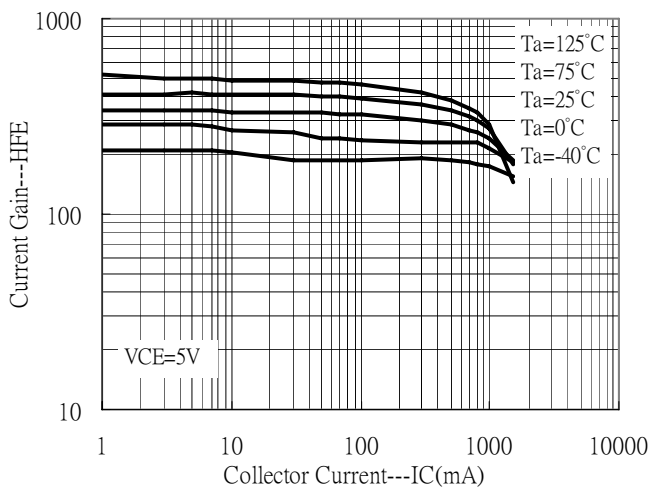
Current Gain vs Collector Current



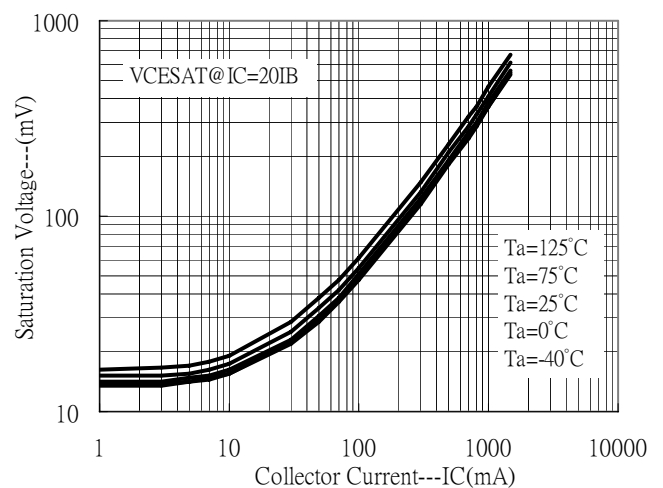
Current Gain vs Collector Current



Current Gain vs Collector Current

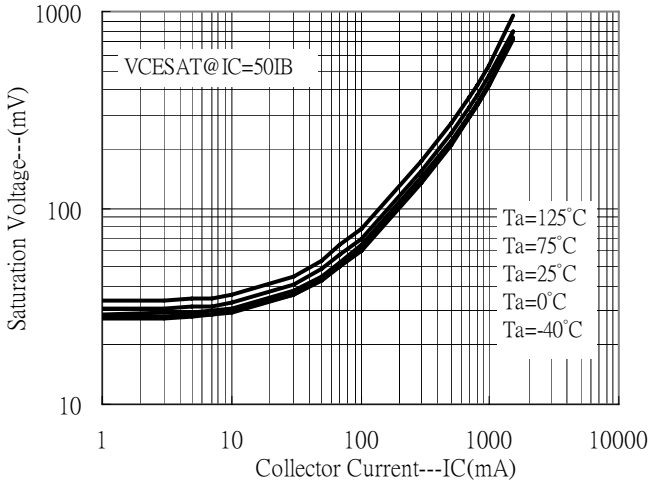


Saturation Voltage vs Collector Current

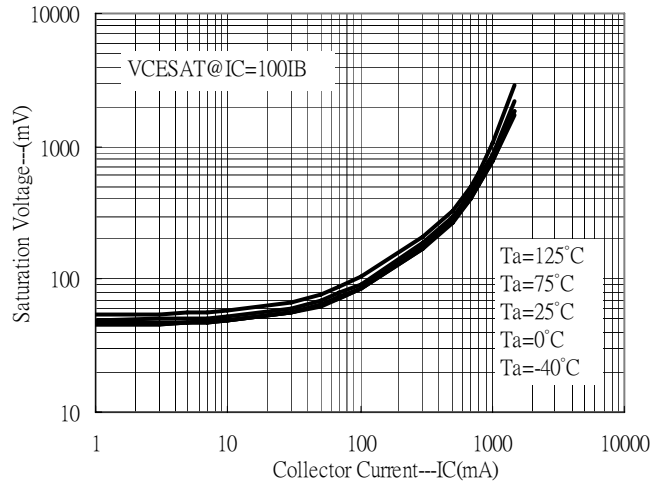


**Typical Characteristics(Cont.)**

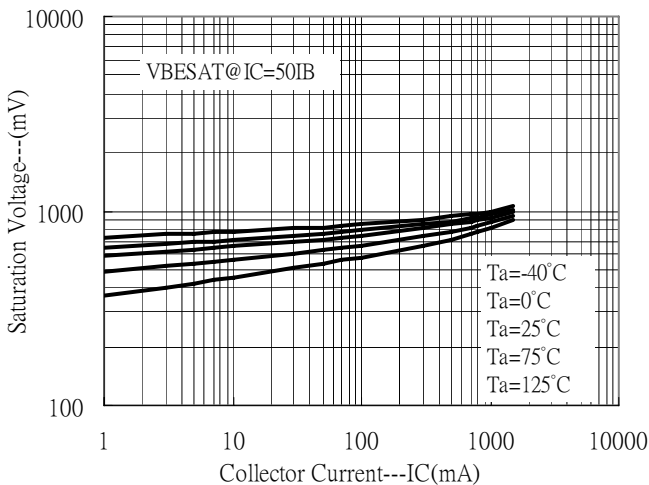
Saturation Voltage vs Collector Current



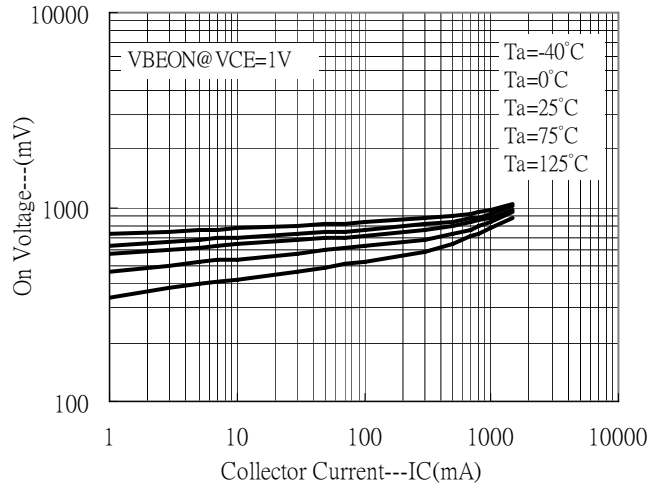
Saturation Voltage vs Collector Current



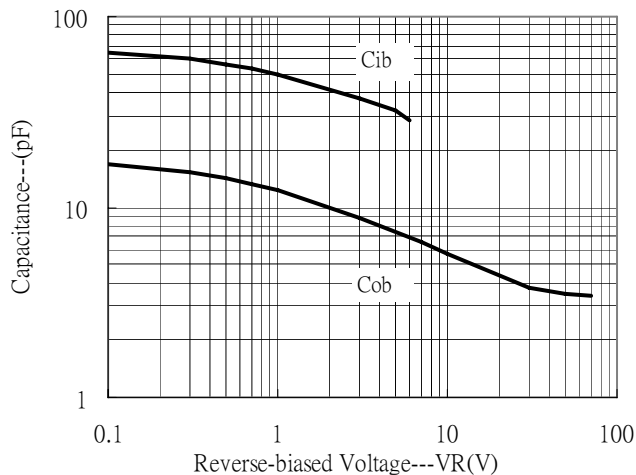
Saturation Voltage vs Collector Current



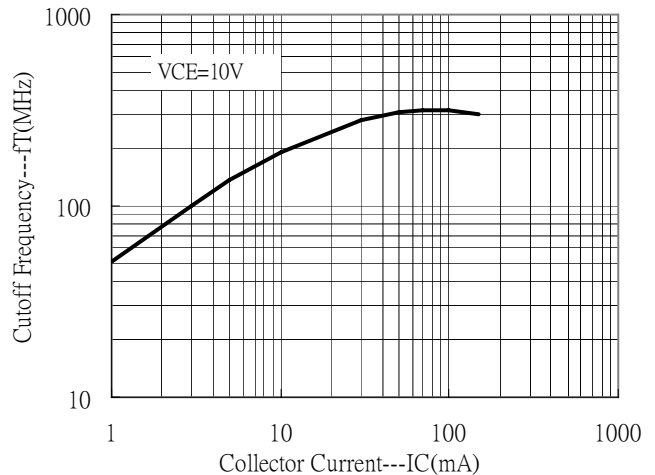
On Voltage vs Collector Current



Capacitance vs Reverse-biased Voltage



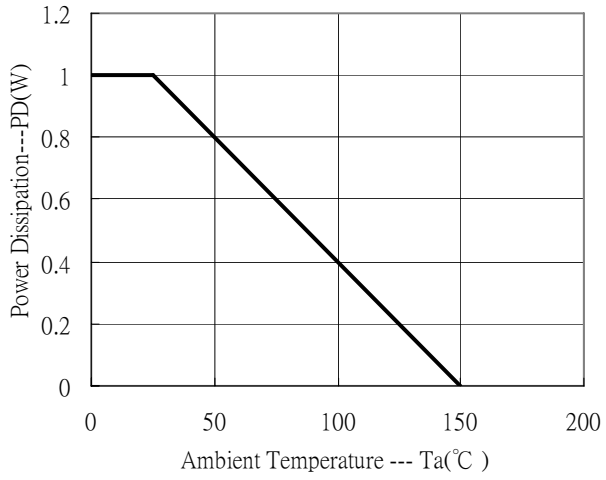
Cutoff Frequency vs Collector Current



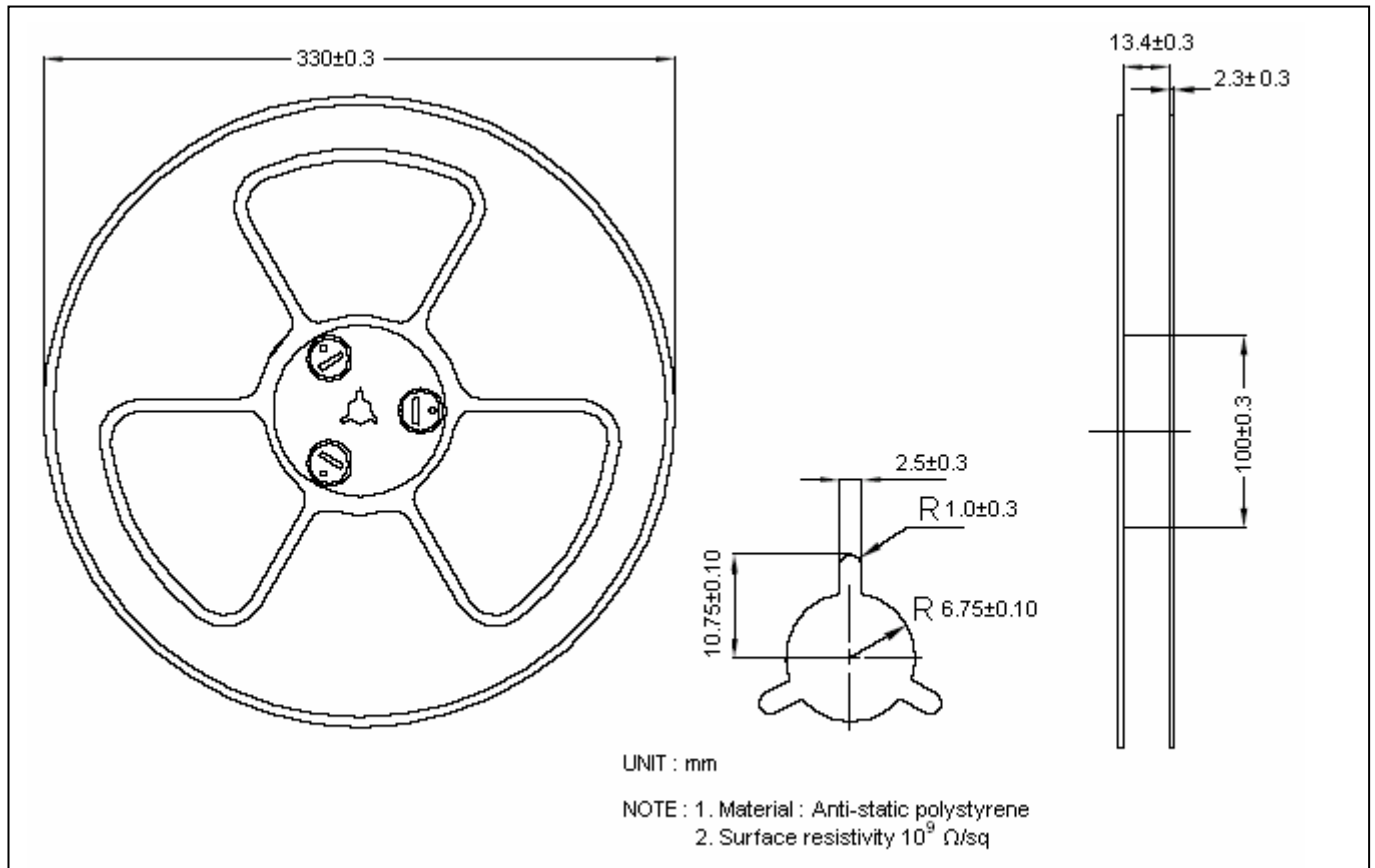


### Typical Characteristics(Cont.)

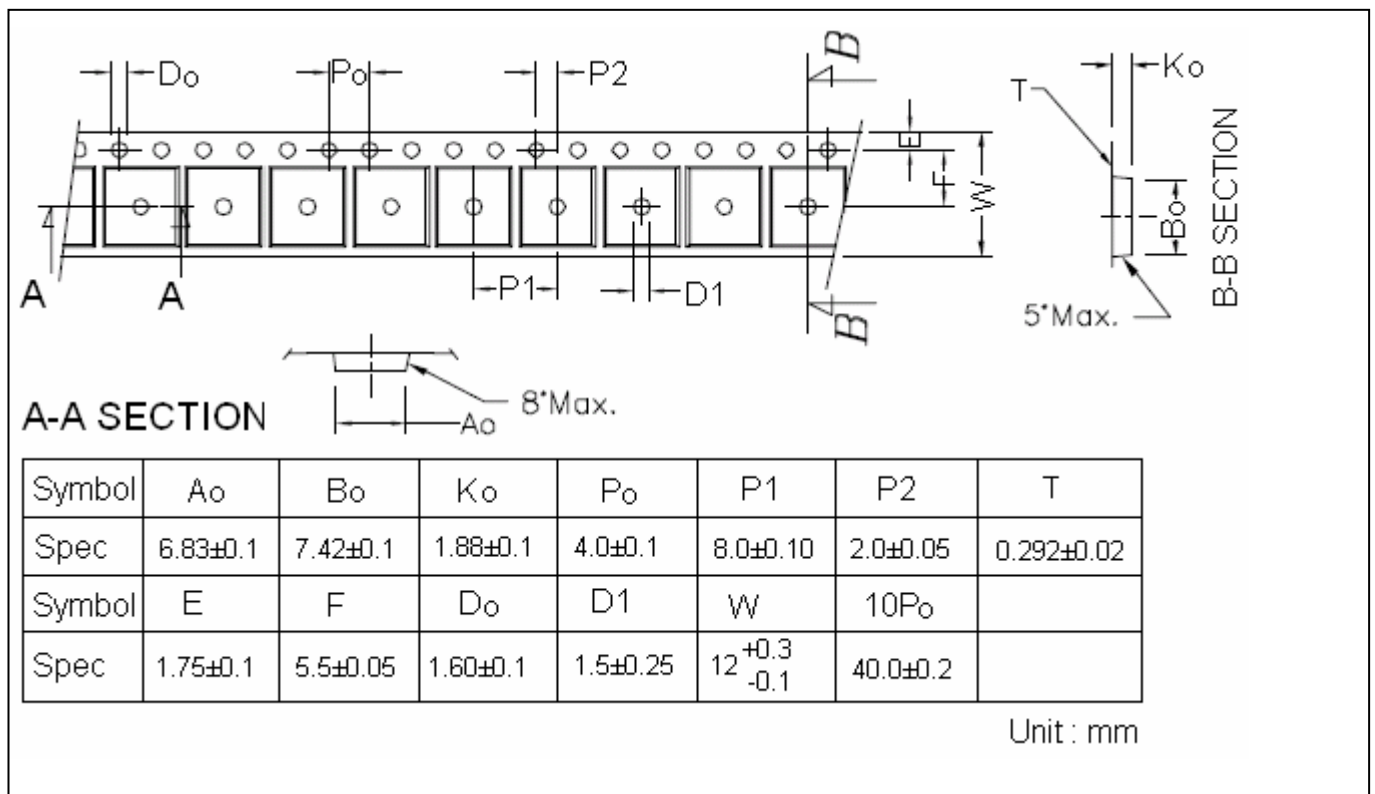
Power Derating Curve



**Reel Dimension**



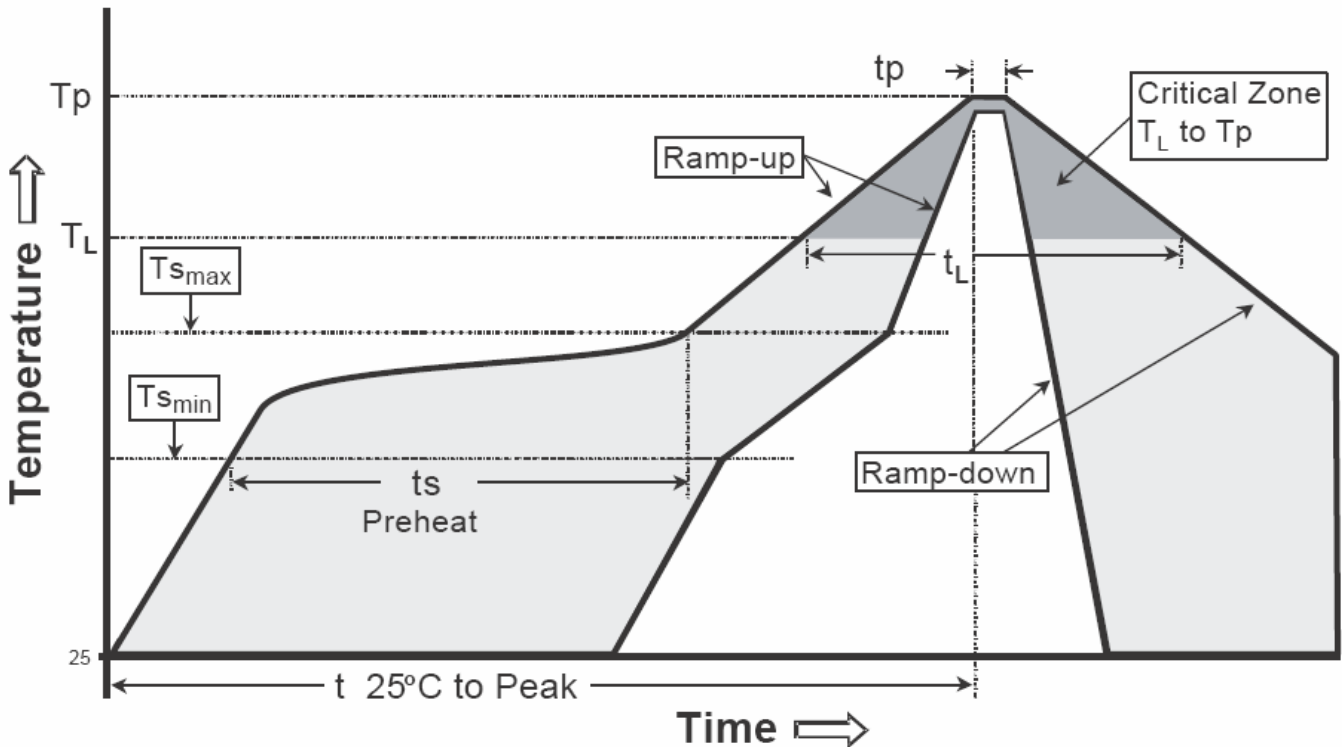
**Carrier Tape Dimension**



**Recommended wave soldering condition**

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

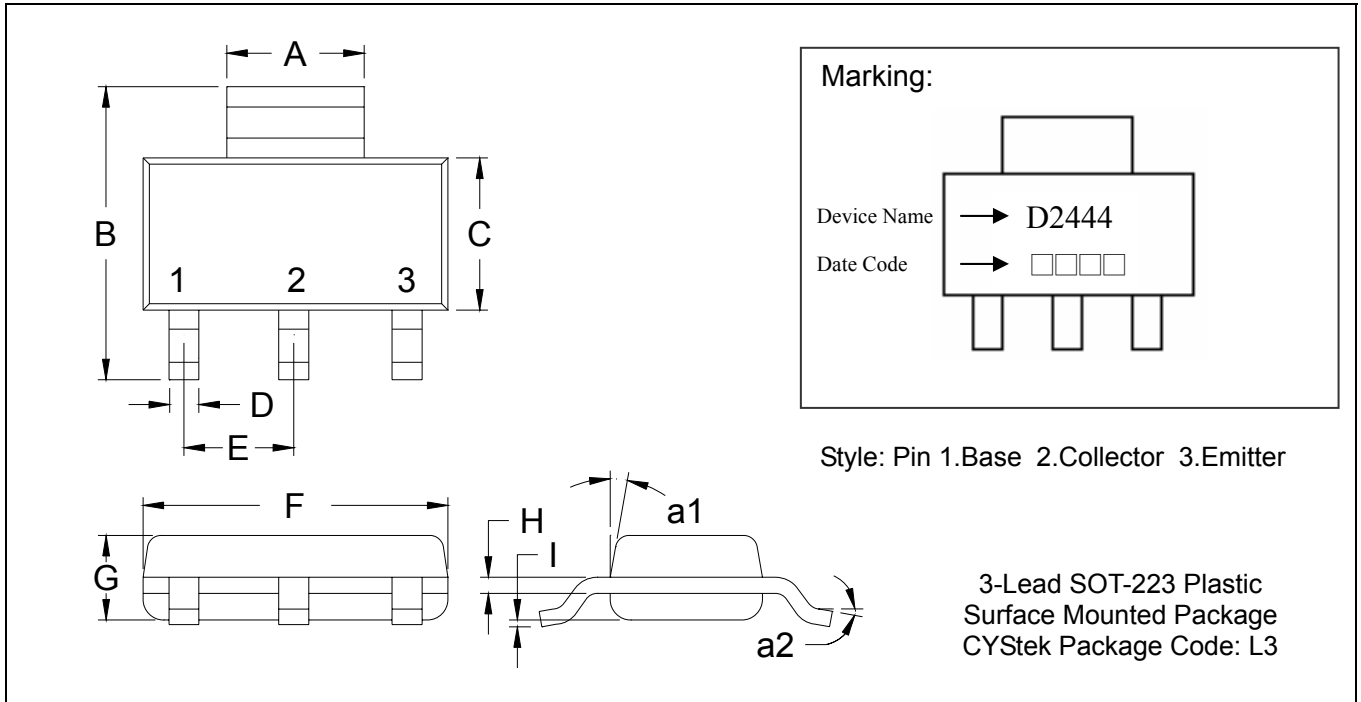
**Recommended temperature profile for IR reflow**



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T <sub>smax</sub> to T <sub>p</sub> )	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(T <sub>s min</sub> )	100°C	150°C
-Temperature Max(T <sub>s max</sub> )	150°C	200°C
-Time(t <sub>s min</sub> to t <sub>s max</sub> )	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T <sub>L</sub> )	183°C	217°C
- Time (t <sub>L</sub> )	60-150 seconds	60-150 seconds
Peak Temperature(T <sub>P</sub> )	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

**SOT-223 Dimension**



\*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1142	0.1220	2.90	3.10	G	0.0551	0.0709	1.40	1.80
B	0.2638	0.2874	6.70	7.30	H	0.0098	0.0138	0.25	0.35
C	0.1299	0.1457	3.30	3.70	I	0.0008	0.0039	0.02	0.10
D	0.0236	0.0315	0.60	0.80	a1	*13°	-	*13°	-
E	*0.0906	-	*2.30	-	a2	0°	10°	0°	10°
F	0.2480	0.2638	6.30	6.70					

- Notes:**
- Controlling dimension: millimeters.
  - Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
  - If there is any question with packing specification or packing method, please contact your local CYStek sales office.

**Material:**

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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